



## Features

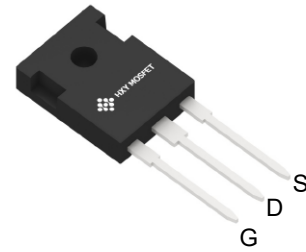
- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Resistant to Latch-Up
- Halogen Free, RoHS Compliant

## Benefits

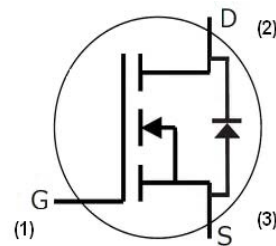
- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

## Applications

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC converters
- Battery Chargers
- Motor Drives
- Pulsed Power Applications



TO-247



| Part Number | Package | Qty(PCS) |
|-------------|---------|----------|
| C2M0025120D | TO-247  | 30       |

## Maximum Ratings ( $T_c = 25^\circ\text{C}$ unless otherwise specified)

| Symbol         | Parameter                                  | Value       | Unit             | Test Conditions                                        | Note              |
|----------------|--------------------------------------------|-------------|------------------|--------------------------------------------------------|-------------------|
| $V_{DSmax}$    | Drain - Source Voltage                     | 1200        | V                | $V_{GS} = 0\text{ V}$ , $I_D = 100\text{ }\mu\text{A}$ |                   |
| $V_{GSmax}$    | Gate - Source Voltage                      | -10/+25     | V                | Absolute maximum values                                |                   |
| $V_{GSop}$     | Gate - Source Voltage                      | -5/+20      | V                | Recommended operational values                         |                   |
| $I_D$          | Continuous Drain Current                   | 63          | A                | $V_{GS} = 20\text{ V}$ , $T_c = 25^\circ\text{C}$      | Fig. 19<br>Note 1 |
|                |                                            | 39          |                  | $V_{GS} = 20\text{ V}$ , $T_c = 100^\circ\text{C}$     |                   |
| $I_{D(pulse)}$ | Pulsed Drain Current                       | 250         | A                | Pulse width $t_p$ limited by $T_{jmax}$                | Fig. 22           |
| $P_D$          | Power Dissipation                          | 378         | W                | $T_c = 25^\circ\text{C}$ , $T_j = 150^\circ\text{C}$   | Fig. 20           |
| $T_j, T_{stg}$ | Operating Junction and Storage Temperature | -55 to +150 | $^\circ\text{C}$ |                                                        |                   |
| $T_L$          | Solder Temperature                         | 260         | $^\circ\text{C}$ | 1.6mm (0.063") from case for 10s                       |                   |
| $M_d$          | Mounting Torque                            | 1<br>8.8    | Nm<br>lbf-in     | M3 or 6-32 screw                                       |                   |

Note (1): Die limits are 90A (25°C) and 60A (100°C)



**Electrical Characteristics** ( $T_c = 25^\circ\text{C}$  unless otherwise specified)

| Symbol        | Parameter                                      | Min. | Typ. | Max. | Unit          | Test Conditions                                                                                                                                                                        | Note       |
|---------------|------------------------------------------------|------|------|------|---------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage                 | 1200 |      |      | V             | $V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$                                                                                                                                    |            |
| $V_{GS(th)}$  | Gate Threshold Voltage                         | 2.0  | 2.6  | 4    | V             | $V_{DS} = V_{GS}, I_D = 15\text{mA}$                                                                                                                                                   | Fig. 11    |
|               |                                                |      | 2.3  |      | V             | $V_{DS} = V_{GS}, I_D = 15\text{mA}, T_J = 150^\circ\text{C}$                                                                                                                          |            |
| $I_{DSS}$     | Zero Gate Voltage Drain Current                |      | 2    | 100  | $\mu\text{A}$ | $V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$                                                                                                                                          |            |
| $I_{GSS}$     | Gate-Source Leakage Current                    |      |      | 250  | nA            | $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$                                                                                                                                            |            |
| $R_{DS(on)}$  | Drain-Source On-State Resistance               |      | 25   | 34   | m $\Omega$    | $V_{GS} = 20\text{ V}, I_D = 50\text{ A}$                                                                                                                                              | Fig. 4,5,6 |
|               |                                                |      | 41   |      |               | $V_{GS} = 20\text{ V}, I_D = 50\text{ A}, T_J = 150^\circ\text{C}$                                                                                                                     |            |
| $g_{fs}$      | Transconductance                               |      | 24.6 |      | S             | $V_{DS} = 20\text{ V}, I_{DS} = 50\text{ A}$                                                                                                                                           | Fig. 7     |
|               |                                                |      | 24   |      |               | $V_{DS} = 20\text{ V}, I_{DS} = 50\text{ A}, T_J = 150^\circ\text{C}$                                                                                                                  |            |
| $C_{iss}$     | Input Capacitance                              |      | 3140 |      | pF            | $V_{GS} = 0\text{ V}$                                                                                                                                                                  | Fig. 17,18 |
| $C_{oss}$     | Output Capacitance                             |      | 224  |      |               | $V_{DS} = 1000\text{ V}$                                                                                                                                                               |            |
| $C_{rss}$     | Reverse Transfer Capacitance                   |      | 9    |      |               | $f = 1\text{ MHz}$                                                                                                                                                                     |            |
| $E_{oss}$     | $C_{oss}$ Stored Energy                        |      | 128  |      | $\mu\text{J}$ | $V_{AC} = 25\text{ mV}$                                                                                                                                                                | Fig 16     |
| $E_{ON}$      | Turn-On Switching Energy (Body Diode)          |      | 2.18 |      | mJ            | $V_{DS} = 800\text{ V}, V_{GS} = -5/20\text{ V},$<br>$I_D = 50\text{ A}, R_{G(ext)} = 2.5\Omega, L = 99\text{ }\mu\text{H}$<br>FWD = Internal Body Diode of MOSFET                     | Fig. 25    |
| $E_{OFF}$     | Turn Off Switching Energy (Body Diode)         |      | 0.68 |      |               |                                                                                                                                                                                        |            |
| $E_{ON}$      | Turn-On Switching Energy (External SiC Diode)  |      | 1.14 |      | mJ            | $V_{DS} = 800\text{ V}, V_{GS} = -5/20\text{ V},$<br>$I_D = 50\text{ A}, R_{G(ext)} = 2.5\Omega, L = 99\text{ }\mu\text{H}$<br>FWD = External SiC Diode                                | Fig. 25    |
| $E_{OFF}$     | Turn Off Switching Energy (External SiC Diode) |      | 0.8  |      |               |                                                                                                                                                                                        |            |
| $t_{d(on)}$   | Turn-On Delay Time                             |      | 15   |      | ns            | $V_{DD} = 800\text{ V}, V_{GS} = -5/20\text{ V}$<br>$I_D = 50\text{ A},$<br>$R_{G(ext)} = 2.5\text{ }\Omega$ , Inductive Load<br>Timing relative to $V_{DS}$<br>Per IEC60747-8-4 pg 83 | Fig. 27    |
| $t_r$         | Rise Time                                      |      | 58   |      |               |                                                                                                                                                                                        |            |
| $t_{d(off)}$  | Turn-Off Delay Time                            |      | 33   |      |               |                                                                                                                                                                                        |            |
| $t_f$         | Fall Time                                      |      | 17   |      |               |                                                                                                                                                                                        |            |
| $R_{G(int)}$  | Internal Gate Resistance                       |      | 1.0  |      | $\Omega$      | $f = 1\text{ MHz}, V_{AC} = 25\text{ mV}, \text{ESR of } C_{iss}$                                                                                                                      |            |
| $Q_{gs}$      | Gate to Source Charge                          |      | 46   |      | nC            | $V_{DS} = 800\text{ V}, V_{GS} = -5/20\text{ V}$<br>$I_D = 50\text{ A}$<br>Per IEC60747-8-4 pg 21                                                                                      | Fig. 12    |
| $Q_{gd}$      | Gate to Drain Charge                           |      | 71.5 |      |               |                                                                                                                                                                                        |            |
| $Q_g$         | Total Gate Charge                              |      | 194  |      |               |                                                                                                                                                                                        |            |

**Reverse Diode Characteristics**

| Symbol        | Parameter                        | Typ. | Max. | Unit | Test Conditions                                                                                                                     | Note          |
|---------------|----------------------------------|------|------|------|-------------------------------------------------------------------------------------------------------------------------------------|---------------|
| $V_{SD}$      | Diode Forward Voltage            | 4.1  |      | V    | $V_{GS} = -5\text{ V}, I_{SD} = 25\text{ A}$                                                                                        | Fig. 8, 9, 10 |
|               |                                  | 3.5  |      | V    | $V_{GS} = -5\text{ V}, I_{SD} = 25\text{ A}, T_J = 150^\circ\text{C}$                                                               |               |
| $I_S$         | Continuous Diode Forward Current |      | 63   |      | $V_{GS} = -5\text{ V}, T_c = 25^\circ\text{C}$                                                                                      | Note 2        |
| $I_{S,pulse}$ | Diode Pulse Current              |      | 250  |      | $V_{GS} = -5\text{ V}$ , Pulse width $t_p$ limited by $T_{Jmax}$                                                                    |               |
| $t_{rr}$      | Reverse Recovery Time            | 33   |      | ns   | $V_{GS} = -5\text{ V}, I_{SD} = 50\text{ A}, T_J = 25^\circ\text{C}$<br>$VR = 800\text{ V}$<br>$dif/dt = 2180\text{ A}/\mu\text{s}$ | Note 2        |
| $Q_{rr}$      | Reverse Recovery Charge          | 487  |      | nC   |                                                                                                                                     |               |
| $I_{rrm}$     | Peak Reverse Recovery Current    | 24   |      | A    |                                                                                                                                     |               |
| $t_{rr}$      | Reverse Recovery Time            | 67   |      | ns   | $V_{GS} = -5\text{ V}, I_{SD} = 50\text{ A}, T_J = 25^\circ\text{C}$<br>$VR = 800\text{ V}$<br>$dif/dt = 1320\text{ A}/\mu\text{s}$ | Note 2        |
| $Q_{rr}$      | Reverse Recovery Charge          | 386  |      | nC   |                                                                                                                                     |               |
| $I_{rrm}$     | Peak Reverse Recovery Current    | 15   |      | A    |                                                                                                                                     |               |

Note (2): When using SiC Body Diode the maximum recommended  $V_{GS} = -5\text{V}$



## Thermal Characteristics

| Symbol          | Parameter                                   | Typ. | Max. | Unit                        | Test Conditions | Note    |
|-----------------|---------------------------------------------|------|------|-----------------------------|-----------------|---------|
| $R_{\theta JC}$ | Thermal Resistance from Junction to Case    | 0.24 | 0.33 | $^{\circ}\text{C}/\text{W}$ |                 | Fig. 21 |
| $R_{\theta JA}$ | Thermal Resistance from Junction to Ambient |      | 40   |                             |                 |         |

## Typical Performance

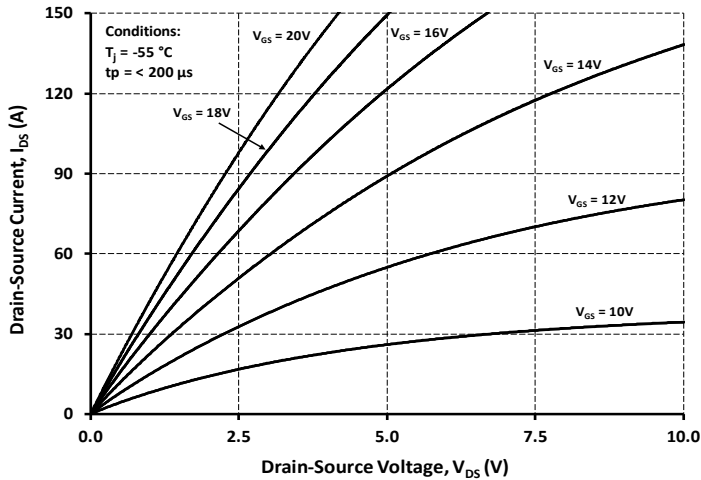


Figure 1. Output Characteristics  $T_J = -55^{\circ}\text{C}$

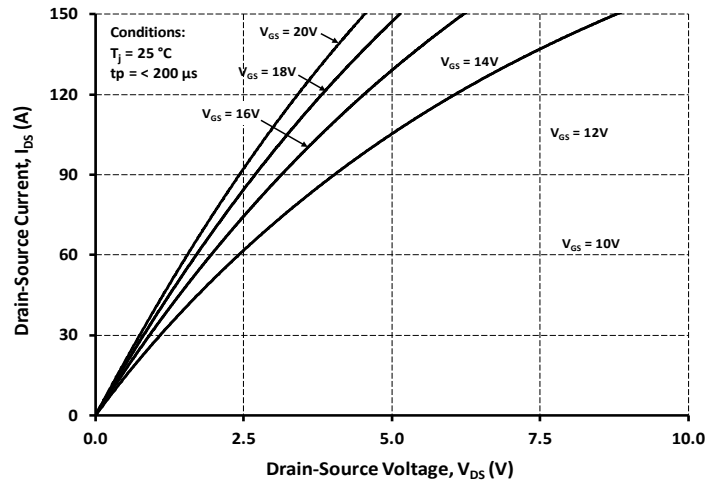


Figure 2. Output Characteristics  $T_J = 25^{\circ}\text{C}$

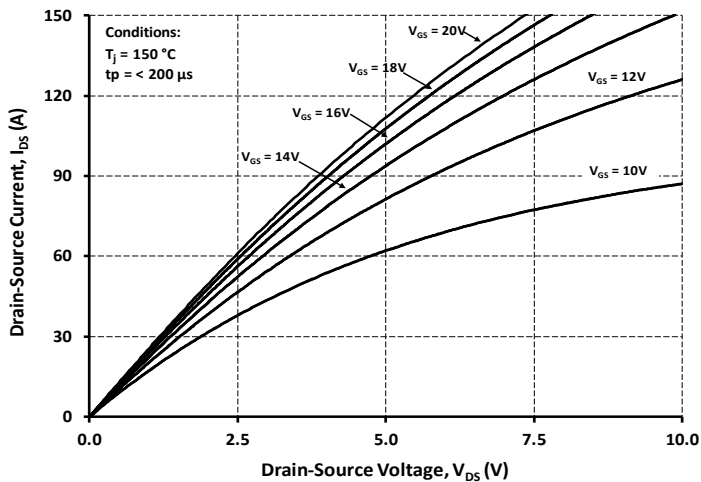


Figure 3. Output Characteristics  $T_J = 150^{\circ}\text{C}$

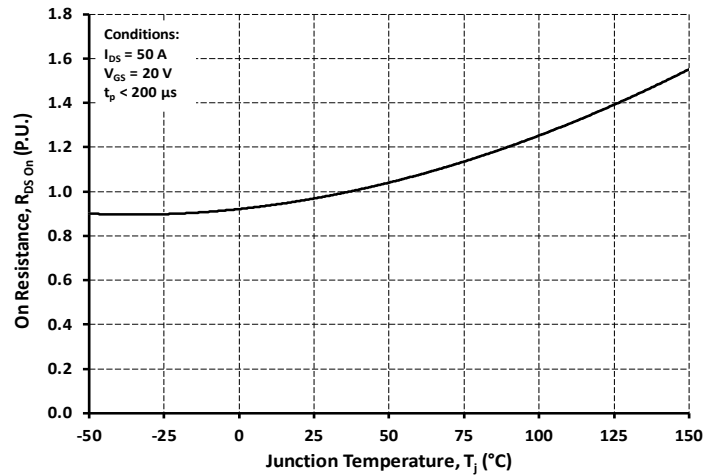


Figure 4. Normalized On-Resistance vs. Temperature

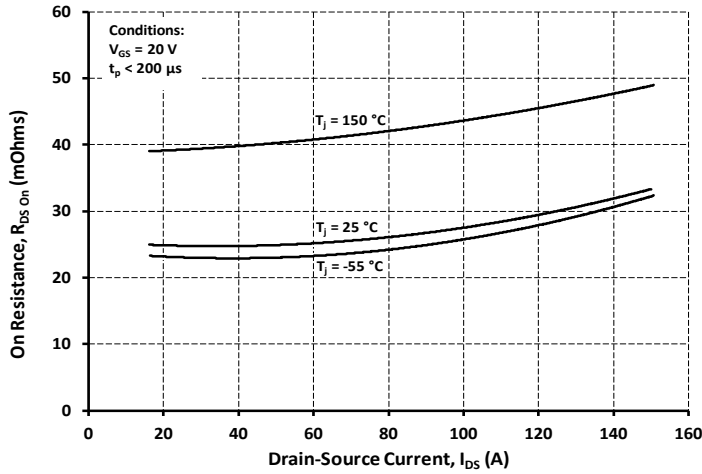


Figure 5. On-Resistance vs. Drain Current  
For Various Temperatures

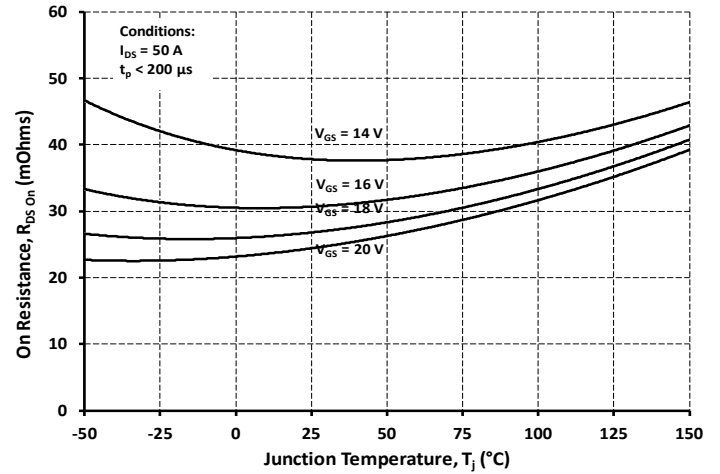


Figure 6. On-Resistance vs. Temperature  
For Various Gate Voltage

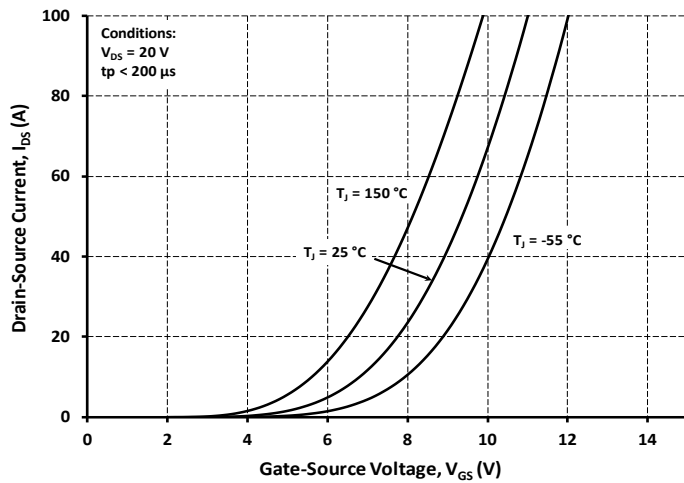


Figure 7. Transfer Characteristic For  
Various Junction Temperatures

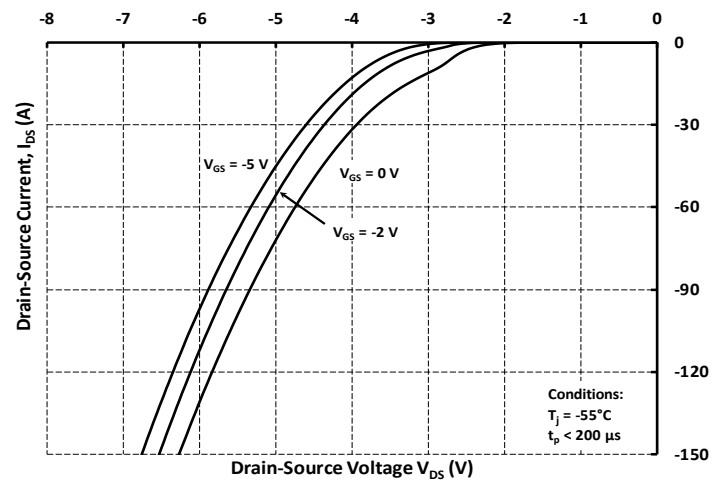


Figure 8. Body Diode Characteristic at  $-55\text{ }^\circ\text{C}$

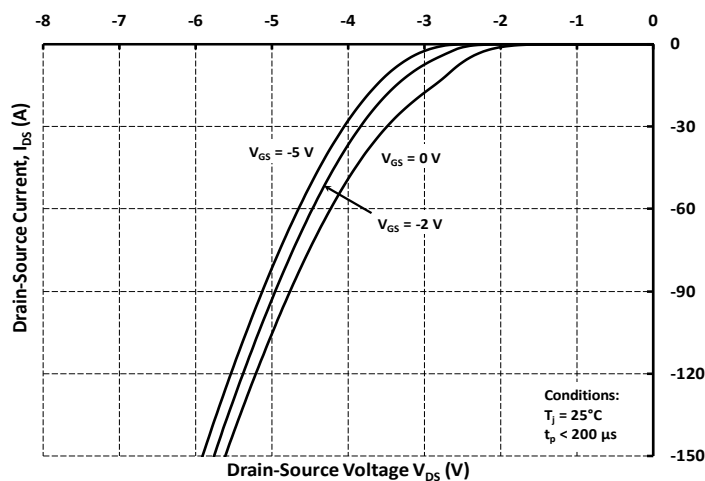


Figure 9. Body Diode Characteristic at  $25\text{ }^\circ\text{C}$

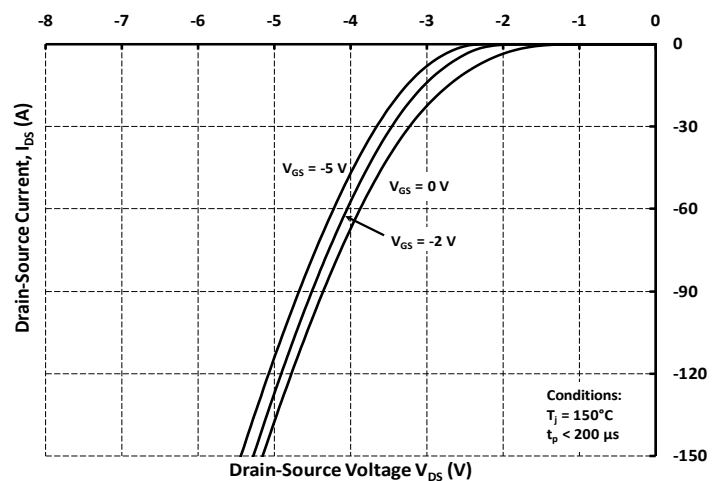


Figure 10. Body Diode Characteristic at  $150\text{ }^\circ\text{C}$

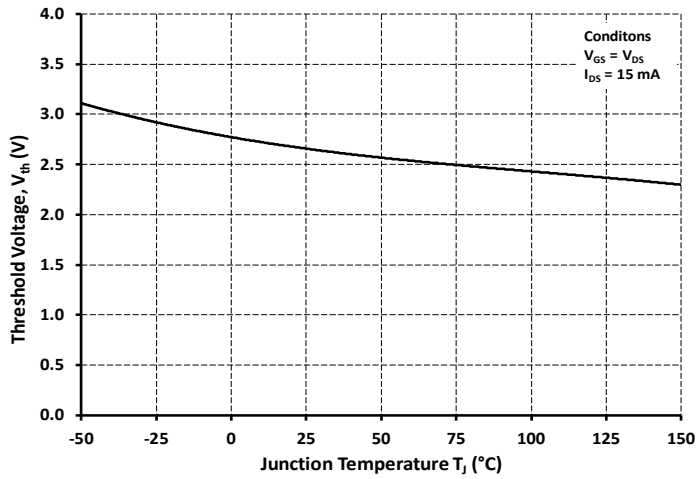


Figure 11. Threshold Voltage vs. Temperature

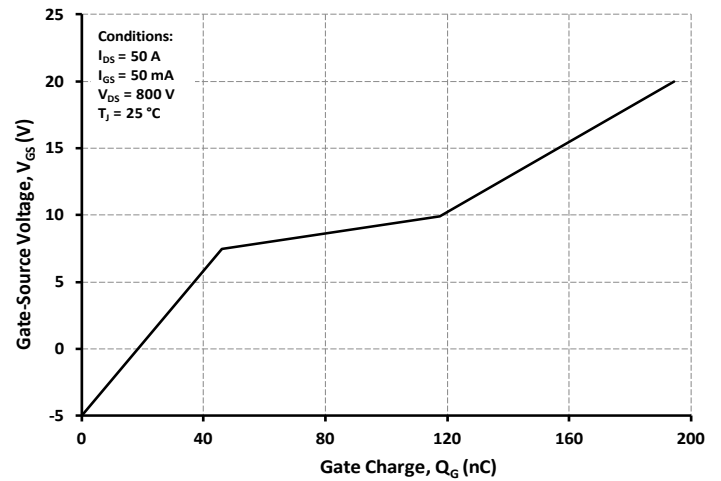


Figure 12. Gate Charge Characteristic

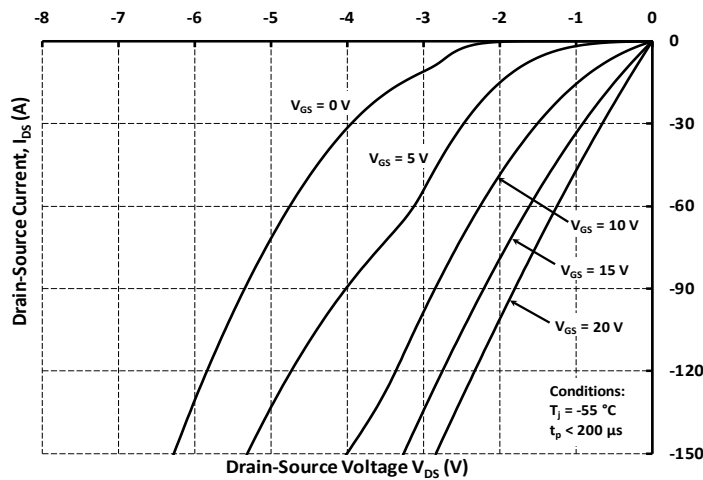


Figure 13. 3rd Quadrant Characteristic at -55 °C

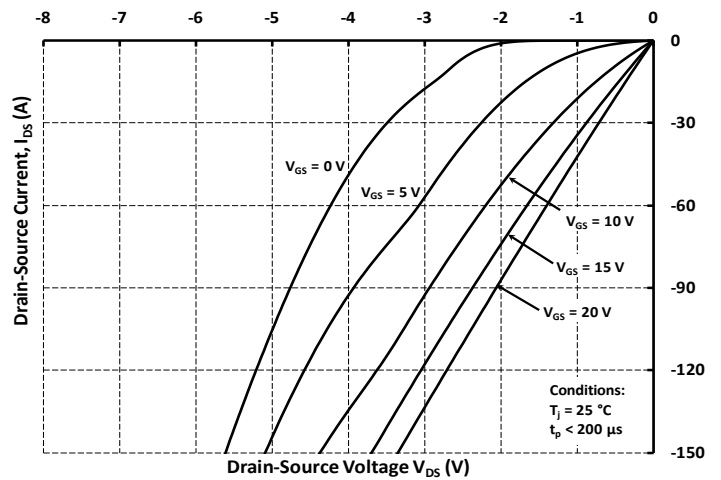


Figure 14. 3rd Quadrant Characteristic at 25 °C

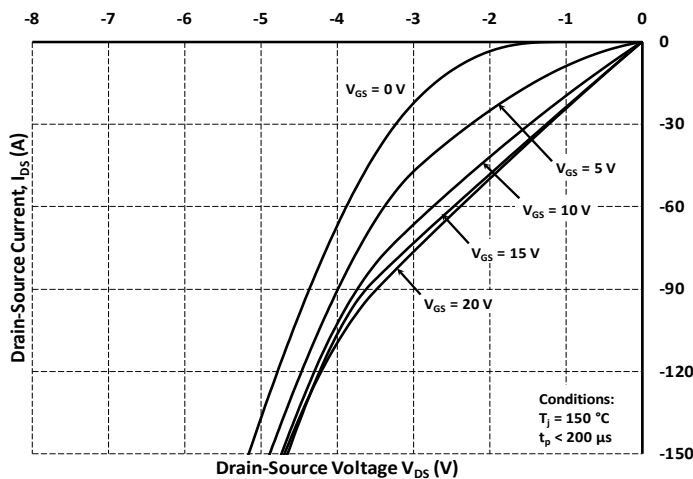


Figure 15. 3rd Quadrant Characteristic at 150 °C

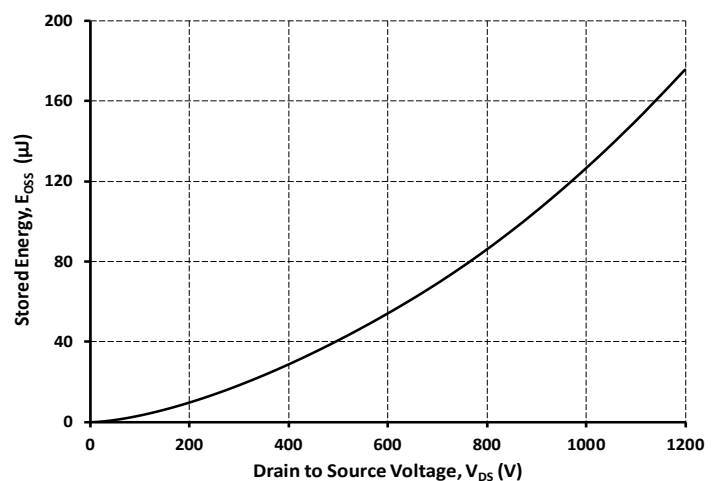
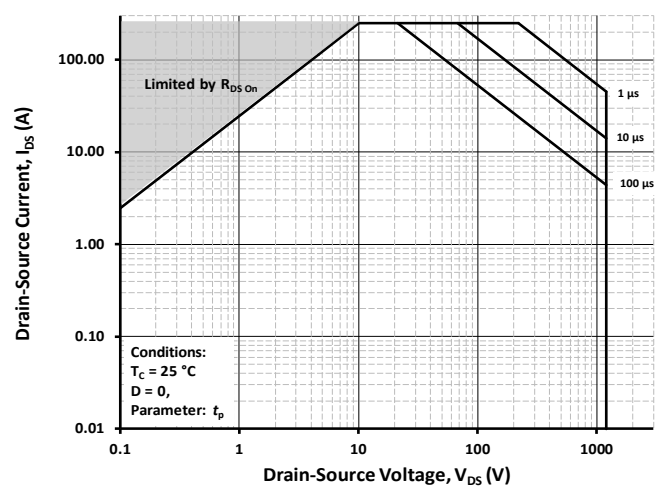
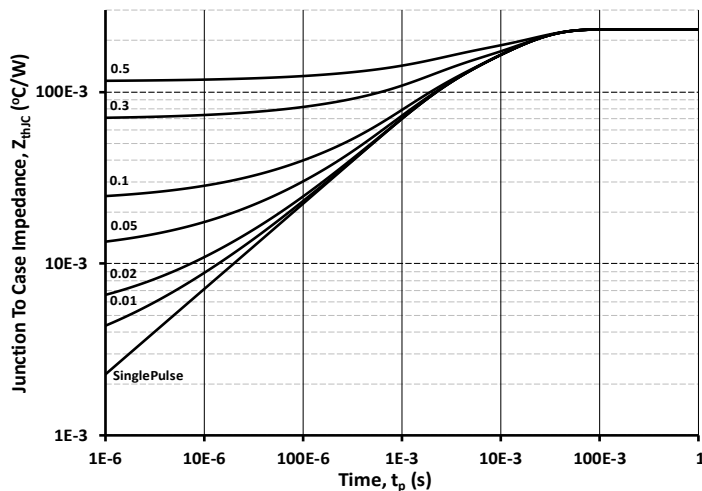
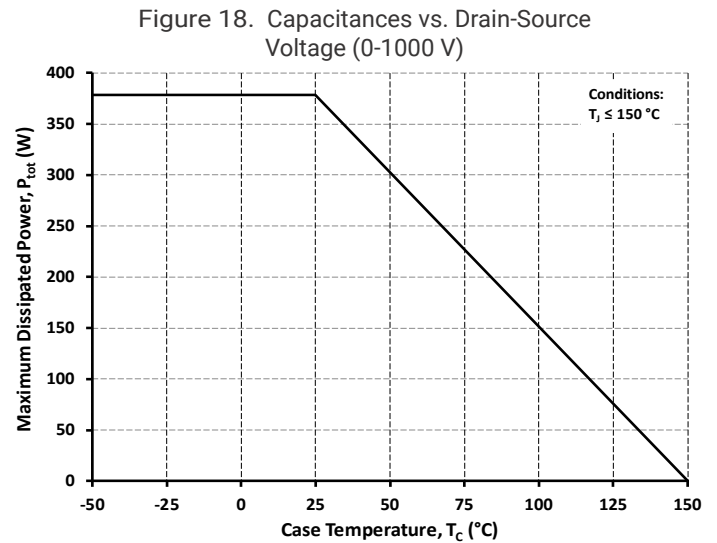
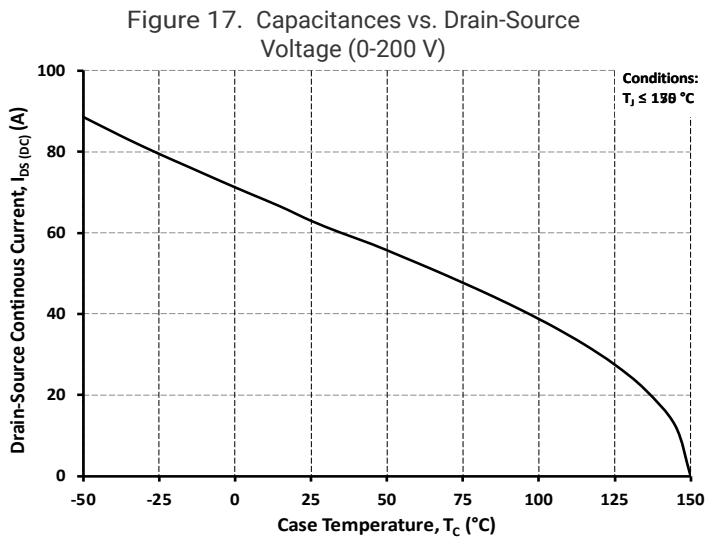
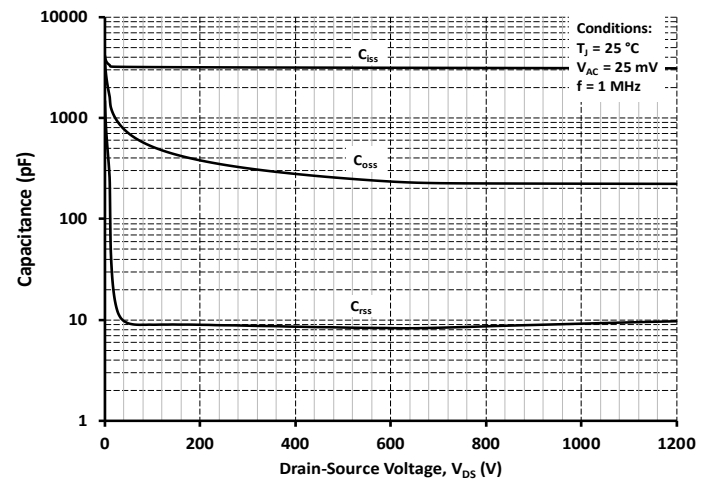
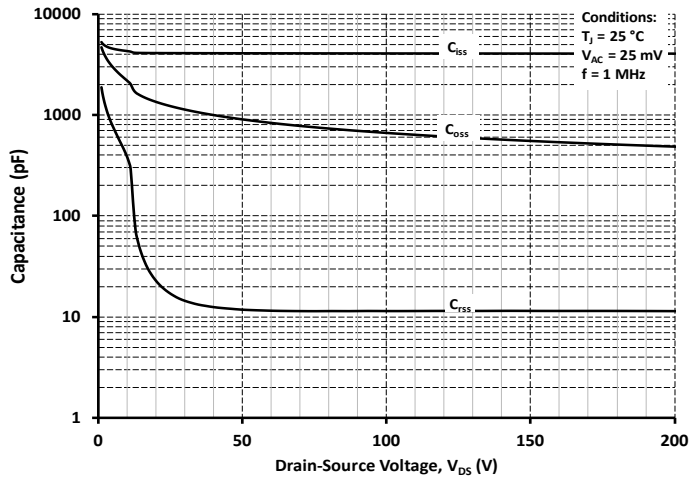


Figure 16. Output Capacitor Stored Energy



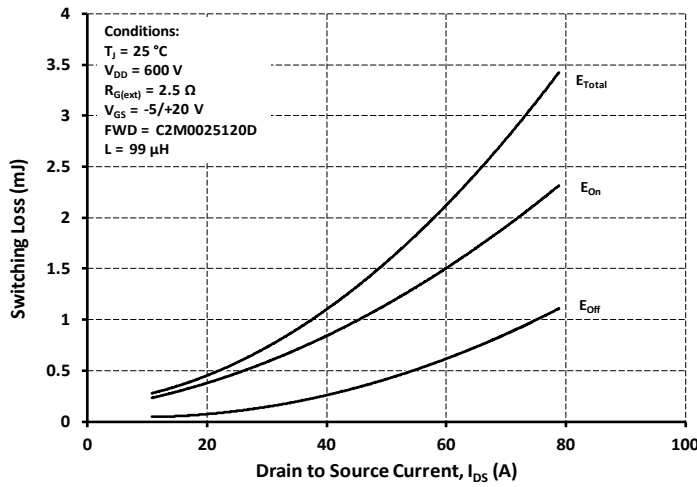


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ( $V_{DD} = 600\text{V}$ )

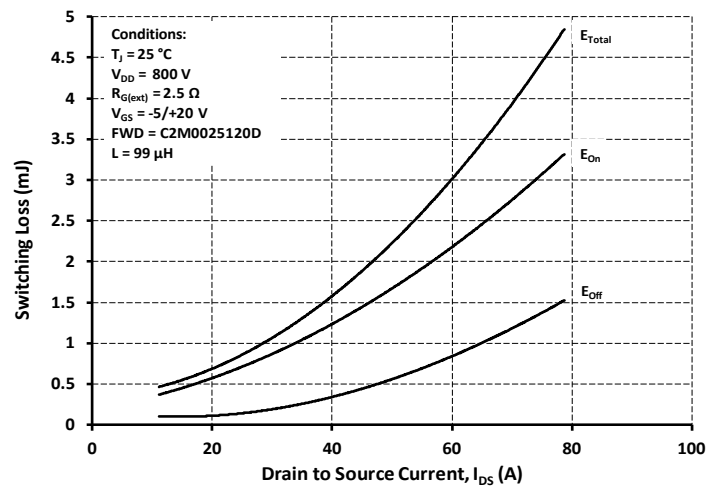


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ( $V_{DD} = 800\text{V}$ )

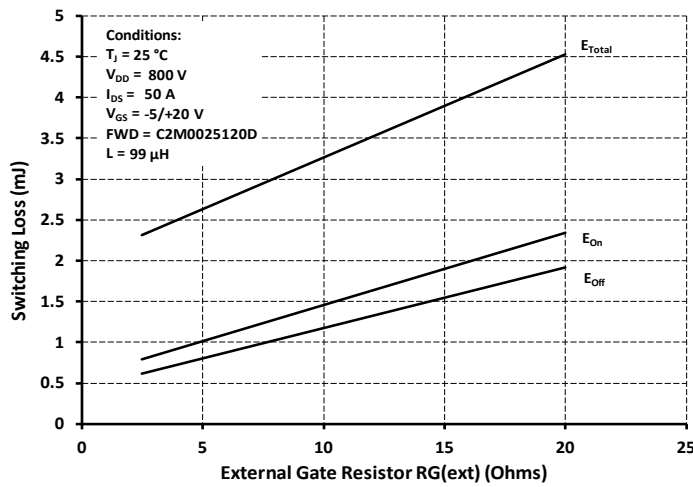


Figure 25. Clamped Inductive Switching Energy vs.  $R_{G(\text{ext})}$

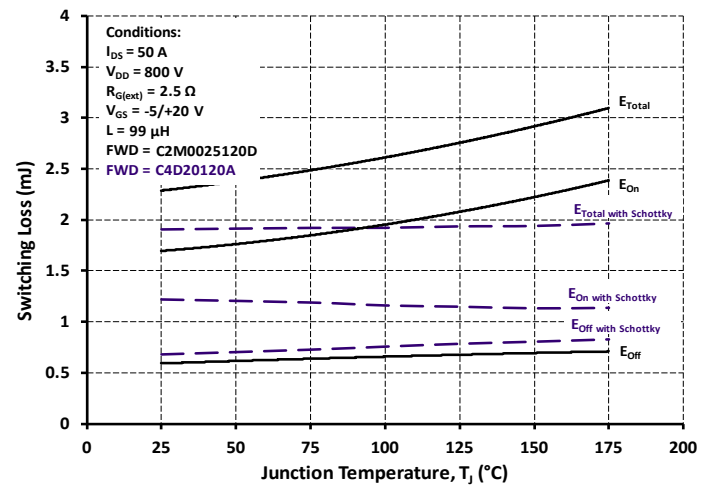


Figure 26. Clamped Inductive Switching Energy vs. Temperature

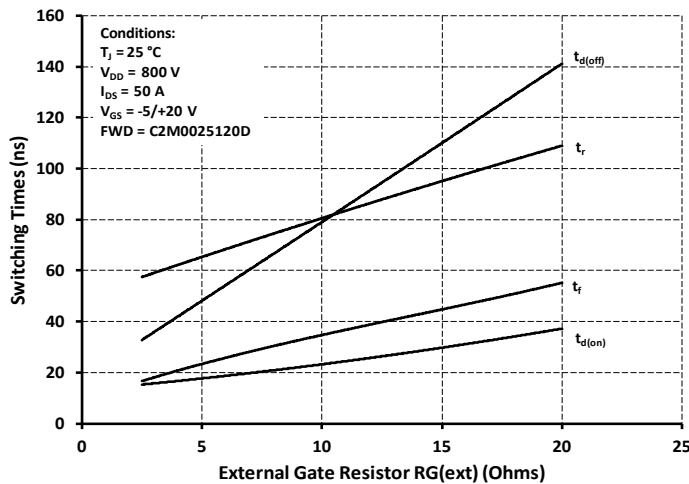


Figure 27. Switching Times vs.  $R_{G(\text{ext})}$

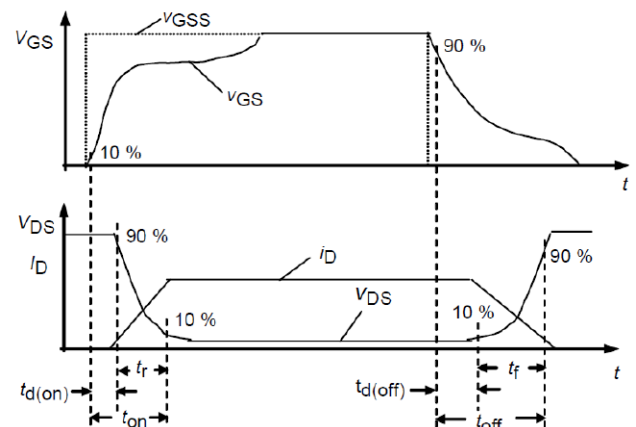
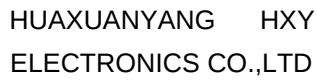


Figure 28. Switching Times Definition

IEC 1161/04



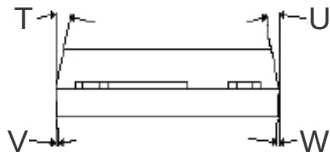
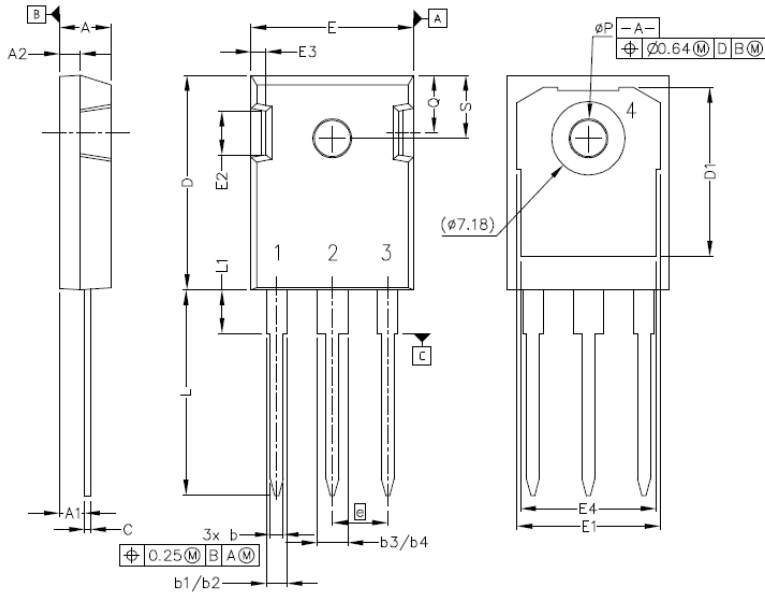
## ESD Ratings

| ESD Test | Resulting Classification |
|----------|--------------------------|
| ESD-HBM  | 3A (4000V - 8000V)       |
| ESD-CDM  | C3 ( $\geq 1000V$ )      |



## Package Dimensions

### Package TO-247

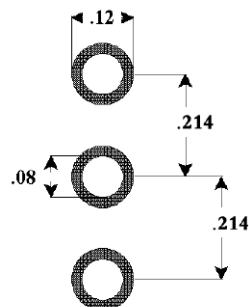


#### Pinout Information:

- Pin 1 = Gate
- Pin 2, 4 = Drain
- Pin 3 = Source

| POS | Inches   |      | Millimeters |       |
|-----|----------|------|-------------|-------|
|     | Min      | Max  | Min         | Max   |
| A   | .190     | .205 | 4.83        | 5.21  |
| A1  | .090     | .100 | 2.29        | 2.54  |
| A2  | .075     | .085 | 1.91        | 2.16  |
| b   | .042     | .052 | 1.07        | 1.33  |
| b1  | .075     | .095 | 1.91        | 2.41  |
| b2  | .075     | .085 | 1.91        | 2.16  |
| b3  | .113     | .133 | 2.87        | 3.38  |
| b4  | .113     | .123 | 2.87        | 3.13  |
| c   | .022     | .027 | 0.55        | 0.68  |
| D   | .819     | .831 | 20.80       | 21.10 |
| D1  | .640     | .695 | 16.25       | 17.65 |
| D2  | .037     | .049 | 0.95        | 1.25  |
| E   | .620     | .635 | 15.75       | 16.13 |
| E1  | .516     | .557 | 13.10       | 14.15 |
| E2  | .145     | .201 | 3.68        | 5.10  |
| E3  | .039     | .075 | 1.00        | 1.90  |
| E4  | .487     | .529 | 12.38       | 13.43 |
| e   | .214 BSC |      | 5.44 BSC    |       |
| N   | 3        |      | 3           |       |
| L   | .780     | .800 | 19.81       | 20.32 |
| L1  | .161     | .173 | 4.10        | 4.40  |
| ØP  | .138     | .144 | 3.51        | 3.65  |
| Q   | .216     | .236 | 5.49        | 6.00  |
| S   | .238     | .248 | 6.04        | 6.30  |
| T   | 9°       | 11°  | 9°          | 11°   |
| U   | 9°       | 11°  | 9°          | 11°   |
| V   | 2°       | 8°   | 2°          | 8°    |
| W   | 2°       | 8°   | 2°          | 8°    |

### Recommended Solder Pad Layout



TO247-3L



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